

**Vishay Siliconix** 

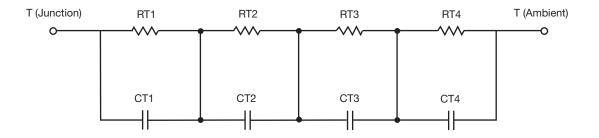
# **R-C Thermal Model Parameters**

#### DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in PSpice, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the PSpice simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the PSpice Platform".

### **R-C THERMAL MODEL FOR TANK CONFIGURATION**



THERMAL RESISTANCE (°C/W)					
Junction to	Ambient	Case	Foot		
RT1	n/a	109.4313m	n/a		
RT2	n/a	158.6130m	n/a		
RT3	n/a	87.6240m	n/a		
RT4	n/a	346.5850m	n/a		
	THERMAL CAPAC	ITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CT1	n/a	33.8943m	n/a		
CT2	n/a	28.7717m	n/a		
CT3	n/a	4.4953m	n/a		
CT4	n/a	75.4153m	n/a		

#### Note

• n/a indicates not applicable

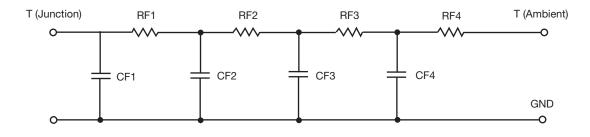
This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

**1** For technical questions, contact: Document Number: 92521



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## **R-C THERMAL MODEL FOR FILTER CONFIGURATION**



R-C VALUES FOR FILTER CONFIGURATION THERMAL RESISTANCE (°C/W)					
RF1	n/a	182.1329m	n/a		
RF2	n/a	106.1598m	n/a		
RF3	n/a	191.3063m	n/a		
RF4	n/a	223.3269m	n/a		
·	THERMAL CAPACI	TANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CF1	n/a	4.0994m	n/a		
CF2	n/a	3.1565m	n/a		
CF3	n/a	22.7911m	n/a		
CF4	n/a	72.6342m	n/a		

Note

• n/a indicates not applicable



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